Supporting Information

3D Graphene Network Encapsulating SnO₂ Hollow Spheres for High-performance Anode Material of Lithium-ion Batteries

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Figure S1. XPS survey spectra (a) of APTEOS modified H-SnO₂ and pure H-SnO₂ samples, and high resolution XPS spectrum of N 1s (b) for the APTEOS modified H-SnO₂ samples. The N 1s peak shows that the primary amines (NH₂, 399.3 eV) and secondary amines (N=C, 398.6 eV) along with oxidized species as amides (NHC=O, 400.9 eV) in the high resolution XPS spectrum. The abundant amino groups can serve as deposition places to coat graphene nanosheets, resulting in graphene fully enwrapped H-SnO₂ nanospheres by electrostatic adsorption.



Figure S2. Zeta potentials of APTEOS modified H-SnO_2 (black square) and graphene oxide (red circle) in aqueous solution at different pH values. The blue rectangle indicates that the assembly process can be spontaneous at pH 2 where the maximum electrostatic interactions are achieved between the APTEOS modified H-SnO_2 and graphene oxide.



Figure S3. Photographs of the assembly process of APTEOS modified H-SnO₂ and graphene oxide in aqueous solutions at pH 2.



Figure S4. The magnified a) FESEM and b) TEM images of the as-prepared H-SnO₂.



Figure S5. a) FESEM and b)TEM images of the solid SnO_2 nanospheres (S-SnO₂) prepared at 150 °C for 6 h. c) FESEM and d) TEM images of after self-assembled wrapping of interconnected graphene networks (S-SnO2@rGO). e) FESEM and f)TEM images of graphene loading hollow SnO_2 nanospheres (H-SnO₂/rGO).



Figure S6. a) XPS of C 1s and b) XPS Sn 3d fine scan spectrum of H-SnO₂@rGO.



Figure S7. The coulombic efficiency of the $H-SnO_2@rGO$ electrode materials at a current density of 0.1 A g⁻¹.



Figure S8. The electrochemical performance of rGO at a current density of 0.1 A g^{-1} .



Figure S9. Cycling performance and Coulombic efficiency of $S-SnO_2@rGO$ for 400 cycles at the current density of 1 A g⁻¹.



Figure S10. a,b) Typical TEM image of a fully charged H-SnO₂@rGO electrode after 100 cycles at a current density of 100 mA g⁻¹.

Table S1. Electrochemical performance comparison of H-SnO₂@rGO with previouslyreported graphene-based SnO₂ composites with different morphologies orcompositions.

Materials	Voltage range(V)	Current density (mA g ⁻¹)	Cycle number	Specific capacity (mAh g ⁻¹)	Reference
H-SnO ₂ @rGO	0.01-3.0	100 1000	100 500	1107 552	Our Work
S-SnO ₂ @rGO	0.01-3.0	100	100	744	Our Work
Graphene-based mesoporous SnO ₂	0.01-3.0	78	50	848	1
SnO ₂ /GNS	0.005-2.0	50	30	570	2
3D SnO ₂ /graphene	0.01-3.0	200	50	845	3
Dually fixed SnO ₂ /G@Pani	0.01-3.0	100	100	770	4
SnO ₂ –GO hybrid	0.005-2.5	100	200	800	5
Graphene nanoribbons/SnO ₂	0.01-2.5	100	50	825	6
3D-G/SnO ₂ @C	0.005-3	100	100	820	7
N-doped G-SnO ₂ Sandwich Papers	0.005-3	50	50	910	8
SnO ₂ Quantum Dots@GO	0.01-3	100	100	1121	9
SnO ₂ /graphene	0.01-2.5	100	200	830	10

SnO ₂ @C@GS	0.01-2	200	100	830	11
SnO ₂ -HNS/G	0.005-3	500	300	696	12
Polyaniline @SnO ₂ @Graphene	0.01-3	1000	100	560	13
SnO ₂ nanosheets @graphene sheets	0.01-1.2	160	50	518	14
SnO ₂ /RGO/C foam	0.01-1.5	130	100	717	15
SnO ₂ quantum dots/RGO	0.01-3	100	200	924	16
rGO/SnO ₂	0.01-3	100	100	536	17
polydopamine- coated RGO/SnO ₂	0.01-2	100	200	718	18
SnO ₂ @G@G	0.01-2	80	120	591	19
graphene/C-SnO ₂	0.005-3	100	50	502	20

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